

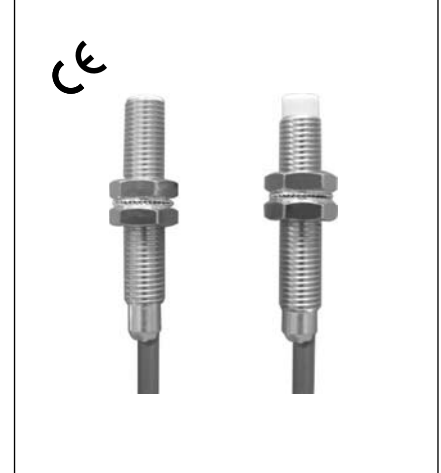
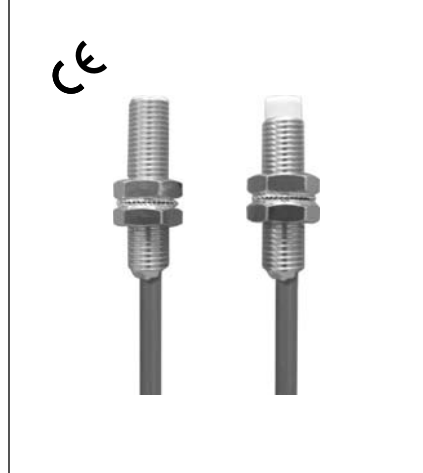
HIGH TEMPERATURE INDUCTIVE PROXIMITY SENSOR (10-30VDC)

Diameter
● Shielded ○ non-Shielded
Switching Distance, Sn: mm
Housing Material
● With LED ○ Without LED

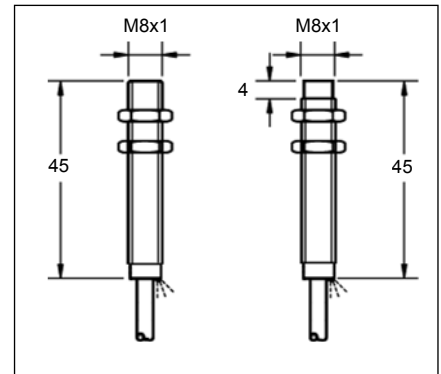
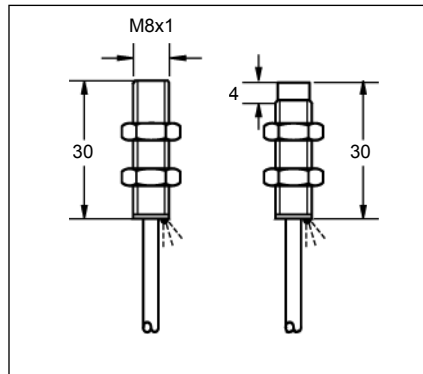
M8	
●	○
1 mm	2 mm
Stainless steel or Nickel plated brass	
●	

M8	
●	○
1 mm	2 mm
Stainless steel or Nickel plated brass	
●	

Picture



Dimensions (unit: mm)



Ripple
No Load Current
Max. Load current
Leakage Current
Voltage Drop
Switching Frequency
Response Time
Switching Hysteresis
Repeat Accuracy
Protection Category
Operating Temperature
Temperature Drift
Short Circuit Protection
Overload Trip Point
Material Active Face

<10%
<10mA
150mA
<0.01mA
<1.5V
2KHz
0.1ms/0.1ms
<15%(Sr)
<1.0%(Sr)
IP67
-25°C - +110°C
<10%(Sr)
Yes
220mA
PTFE

<10%
<10mA
150mA
<0.01mA
<1.5V
2KHz
0.1ms/0.1ms
<15%(Sr)
<1.0%(Sr)
IP67
-25°C - +110°C
<10%(Sr)
Yes
220mA
PTFE

Connecting type
Weight

2M Silicon Cable (4.0 φ 3x0.25)
approx.40 g

2M Silicon Cable (4.0 φ 3x0.25)
approx.53 g

DC 3 wire 10-30V NPN N.O.
DC 3 wire 10-30V NPN N.C.
DC 3 wire 10-30V PNP N.O.
DC 3 wire 10-30V PNP N.C.
DC 3 wire 10-55V NPN N.O.
DC 3 wire 10-55V NPN N.C.
DC 3 wire 10-55V PNP N.O.
DC 3 wire 10-55V PNP N.C.
DC 3 wire 5-36 V NPN N.O.
DC 3 wire 5-36 V NPN N.C.
DC 3 wire 5-36 V PNP N.O.
DC 3 wire 5-36 V PNP N.C.

ISS-M801N-A1SS2/T	1*	ISN-M802N-A1SS2/T
ISS-M801N-B1SS2/T	2	ISN-M802N-B1SS2/T
ISS-M801P-A1SS2/T	3	ISN-M802P-A1SS2/T
ISS-M801P-B1SS2/T	4	ISN-M802P-B1SS2/T

ISS-M801N-A1SN2/T	1*	ISN-M802N-A1SN2/T
ISS-M801N-B1SN2/T	2	ISN-M802N-B1SN2/T
ISS-M801P-A1SN2/T	3	ISN-M802P-A1SN2/T
ISS-M801P-B1SN2/T	4	ISN-M802P-B1SN2/T

* Wiring diagram number. Please see the relevant wiring diagram shown on Page 013 and Page 014.